

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 2

**IN THE CLAIMS:**

1. (Currently Amended) A magnetoresistive sensor including a substrate, a pair of magnetic shield layers consisting of a lower magnetic shield layer and an upper magnetic shield layer, a magnetoresistive sensor layer disposed between the pair of magnetic shields, an electrode terminal for flowing a signal current perpendicular to the plane of the magnetoresistive sensor layer, and magnetic domain control layers for controlling Barkhausen noise of said magnetoresistive sensor layer, wherein said magnetic domain control layers disposed on opposite ends of the magnetoresistive sensor layer in a region from the end surface of a media-opposed surface side of the magnetoresistive sensor layer to the depth position are made of a material having a specific resistance not less than 10 mΩcm, and are in contact with at least opposite end surfaces of said magnetoresistive sensor layer in said region;

wherein ~~a material consisting of said~~ each magnetic domain control layer ~~is a granular layer made by mixing a~~ of said magnetic domain control layers includes regions of hard magnetic material having high coercivity made of a metal magnetic material having a composition including at least one of the elements of Co (cobalt), Cr (chromium), Pt (platinum), Ta (tantalum), and Nb (niobium), and regions of ~~with an~~ insulating material made of at least one of Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, HfO<sub>2</sub>, TaO<sub>2</sub>, TiO<sub>2</sub>, Ta<sub>2</sub>O<sub>5</sub>, AlN, AlSiN, or ZrO<sub>2</sub>, said each magnetic domain control layer including at least two of the regions of hard magnetic material which are separated from one another.

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 3

2. (Withdrawn) The magnetoresistive sensor according to claim 1, comprising magnetic yoke layers disposed between the pair of magnetic shields, having a shape extended from the position exposed from the media-opposed surface in the depth direction, and guiding the magnetic field of the recording media to its interior, wherein said magnetoresistive sensor layer is disposed between the magnetic yoke layers in the position recessed from the media-opposed surface, said magnetic domain control layers are provided on opposite ends of the magnetoresistive sensor layer in a region from the end surface of the media-opposed surface side of the magnetoresistive sensor layer and the magnetic yoke layer to the depth position and are in contact with at least opposite end surfaces of said magnetoresistive sensor layer in said region, and the magnetic domain control layers are in contact with opposite end surfaces of said magnetic yoke layer in at least one portion of the region from the end surface of the media-opposed surface side of said magnetic yoke layer to the depth position.

3. (Currently Amended) The magnetoresistive sensor according to claim 1, comprising a flux guide type magnetic yoke layer disposed between the pair of magnetic shields, having a shape extended from the position exposed from the media-opposed surface in the depth position, and being in contact with any one of the magnetic shield layers to guide the magnetic flux of the media, and said magnetic domain control layers for controlling Barkhausen noise of the magnetoresistive sensor layer and the flux guide type magnetic yoke layer, wherein said magnetoresistive sensor layer is disposed at the upper or lower side of said flux

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 4

guide type yoke layer in the position recessed from the media-opposed surface, the flux guide type yoke layer has an discontinuous portion in a region in contact with said magnetoresistive sensor layer, said magnetic domain control layers disposed on opposite ends of the magnetoresistive sensor layer in the region from the end surface of the media-opposed surface side of said magnetoresistive sensor layer and said flux guide type magnetic yoke layer to the depth position are in contact with at least opposite end surfaces of said magnetoresistive sensor layer in the region from the end surface of the media-opposed surface side of said magnetoresistive sensor layer to the depth position, and the magnetic domain control layers are in contact with opposite end surfaces of said magnetic yoke layer in at least one portion of the region from the end surface of media-opposed surface side of said magnetic yoke layer to the depth position.

4. (Currently Amended) The magnetoresistive sensor according to claim 1, wherein said magnetic domain control layer ~~is made of~~ includes an underlayer made of an oxide having a thickness not more than 5 nm, and an oxide material having high electric resistivity not less than 10 mΩcm formed on the oxide underlayer.

5. (Currently Amended) The magnetoresistive sensor according to claim 2, wherein said magnetic domain control layer ~~is made of~~ includes an underlayer made of an oxide having a thickness not more than 5 nm, and an oxide material having high electric resistivity not less than 10 mΩcm formed on the oxide underlayer.

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 5

6. (Currently Amended) The magnetoresistive sensor according to claim 3, wherein said magnetic domain control layer ~~is made of~~ includes an underlayer made of an oxide having a thickness not more than 5 nm, and an oxide material having high electric resistivity not less than 10 mΩcm formed on the oxide underlayer.

7.-14. (Cancelled)

15. (Withdrawn) The magnetoresistive sensor according to claim 1, wherein said magnetic domain control layer is at least partially superimposed on the plane of said magnetoresistive sensor layer.

16. (Withdrawn) The magnetoresistive sensor according to claim 1, wherein said magnetoresistive sensor layer is a tunnel magnetoresistive sensor layer.

17. (Withdrawn) A combined magnetic head mounting a write element and a read element, wherein the read element comprises the magnetoresistive sensor according to claim 1.

18.-20. (Cancelled)

21. (Currently Amended) A magnetoresistive sensor including a substrate, a pair of magnetic shield layers consisting of a lower magnetic shield layer and an upper magnetic shield layer, a magnetoresistive sensor layer disposed between the

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 6

pair of magnetic shields, an electrode terminal for flowing a signal current perpendicular to the plane of the magnetoresistive sensor layer, and magnetic domain control layers, wherein ~~a material consisting of said a~~ magnetic domain control layer of said magnetic domain control layers is disposed on each of two opposite ends of the magnetoresistive sensor layer in the region from the end surface of the media-opposed surface side of the magnetoresistive sensor layer to the depth position, ~~is a granular layer made by mixing wherein each said magnetic domain control layer includes regions of~~ a hard magnetic material having high coercivity made of a metal magnetic material having a composition including at least one of the elements of Co (cobalt), Cr (chromium), Pt (platinum), Ta (tantalum), and Nb (niobium), and regions of with an insulating material made of at least one of Al<sub>2</sub>O<sub>3</sub>, SiO<sub>2</sub>, HfO<sub>2</sub>, TaO<sub>2</sub>, TiO<sub>2</sub>, Ta<sub>2</sub>O<sub>5</sub>, AlN, AlSiN, or ZrO<sub>2</sub>, each said magnetic domain control layer including at least two of the regions of hard magnetic material which are separated from one another.

22. (Currently Amended) A magnetoresistive sensor including a substrate, a pair of magnetic shield layers consisting of a lower magnetic shield layer and an upper magnetic shield layer, a magnetoresistive sensor layer disposed between the pair of magnetic shields, an electrode terminal for flowing a signal current perpendicular to the plane of the magnetoresistive sensor layer, and magnetic domain control layers, wherein ~~said a~~ magnetic domain control layer of said magnetic domain control layers is disposed on each of opposite ends of the magnetoresistive sensor layer in the region from the end surface of the media-opposed surface side of the magnetoresistive sensor layer to the depth position

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 7

~~comprises~~ and includes a layer made of a soft magnetic material having high electric resistivity disposed in contact with opposite ends of said magnetoresistive sensor layer, and a hard magnetic layer, disposed outside the soft magnetic material, made of a metal magnetic material having a composition including at least one of the elements of Co (cobalt), Cr (chromium), Pt (platinum), Ta (tantalum), and Nb (niobium).

23. (Currently Amended) A magnetoresistive sensor including a substrate, a pair of magnetic shield layers consisting of a lower magnetic shield layer and an upper magnetic shield layer, a magnetoresistive sensor layer disposed between the pair of magnetic shields, an electrode terminal for flowing a signal current perpendicular to the plane of the magnetoresistive sensor layer, and magnetic domain control layers for controlling Barkhausen noise of said magnetoresistive sensor layer, wherein a magnetic domain control layer of said magnetic domain control layers is disposed on opposite ends of the magnetoresistive sensor layer in a region from the end surface of a media-opposed surface side of the magnetoresistive sensor layer to the depth position are made of a material having a specific resistance not less than 10 mΩmn, ~~and are~~ in contact with at least opposite end surfaces of said magnetoresistive sensor layer in said region;

wherein said magnetic domain control layer comprises a layer made of a soft magnetic material having high electric resistivity disposed in contact with opposite ends of said magnetoresistive sensor layer, and a hard ~~high~~ magnetic layer, disposed outside the soft magnetic material, made of a metal magnetic material having a composition including at least one of the elements of Co (cobalt), Cr (chromium), Pt (platinum), Ta (tantalum), and Ni (niobium).

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 8

24. (Withdrawn) The magnetoresistive sensor according to Claim 23, wherein said magnetic domain control layer is at least partially superimposed on the plane of said magnetoresistive sensor layer.

25. (Withdrawn) The magnetoresistive sensor according to Claim 23, wherein said magnetoresistive sensor layer is a tunnel magnetoresistive layer.

26. (Currently Amended) A magnetoresistive sensor comprising:

a magnetoresistive sensor layer; and

a magnetic domain control layer on each of two opposite end surfaces of said magnetoresistive layer, each magnetic control layer in contact with end surfaces of said magnetoresistive layer and having a specific resistance of not less than 10mΩcm, and including regions made of a metal magnetic material having a composition including at least one of the elements of Co (cobalt), Cr (chromium), Pt (platinum), Ta (tantalum), and Ni (niobium), said each magnetic domain control layer including at least two of the regions of hard magnetic material which are separated from one another.

27. (New) The magnetoresistive sensor according to claim 1, wherein the material consisting of said magnetic domain control layer is a granular layer.

28. (New) The magnetoresistive sensor according to claim 21, wherein the material consisting of said magnetic domain control layer is a granular layer.

TAKAHASHI *et al.*, 09/811,606  
Suppl. Amdt. filed 12 August 2004  
Responsive to Ex. Intv. of 11 August 2004

520.39871X00/NT0318US1  
Page 9

29. (New) The magnetoresistive sensor according to claim 22, wherein at least one of the layer and hard magnetic layer of the magnetic domain control layer is a granular layer.

30. (New) The magnetoresistive sensor according to claim 23, wherein at least one of the layer and hard magnetic layer of the magnetic domain control layer is a granular layer.

31. (New) The magnetoresistive sensor according to claim 26, wherein the magnetic domain control layer is a granular layer.

32. (New) The magnetoresistive sensor according to claim 22, wherein the hard magnetic layer is disposed separated from the soft magnetic material.

33. (New) The magnetoresistive sensor according to claim 23, wherein the hard magnetic layer is disposed separated from the soft magnetic material.